Complementary Plastic Silicon Power Transistors

... designed for low power audio amplifier and low current, high speed switching applications.

Collector–Emitter Sustaining Voltage —

VCEO(sus) = 60 Vdc — MJE171, MJE181 = 80 Vdc — MJE172, MJE182

• DC Current Gain -

 $h_{FE} = 30 \text{ (Min)} @ I_{C} = 0.5 \text{ Adc}$

= 12 (Min) @ IC = 1.5 Adc

Current–Gain — Bandwidth Product —

fT = 50 MHz (Min) @ IC = 100 mAdc

 Annular Construction for Low Leakages — ICBO = 100 nA (Max) @ Rated V_{CB}

MAXIMUM RATINGS

Rating	Symbol	MJE171 MJE172 MJE181 MJE182		Unit
Collector-Base Voltage	VCB	80	Vdc	
Collector–Emitter Voltage	VCEO	60 80 🦏		Vdc
Emitter–Base Voltage	V _{EB}	7.	Vdc	
Collector Current — Continuous Peak	lC	3.0 6.0		Adc
Base Current	IB	1.0		Adc
Total Power Dissipation @ T _A = 25°C Derate above 25°C	PD	1.5 0.012		Watts W/°C
Total Power Dissipation @ T _C = 25°C Derate above 25°C	PD	12.5 0.1		Watts W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θJC	10	°C/W
Thermal Resistance, Junction to Ambient	θ.ΙΑ	83.4	°C/W

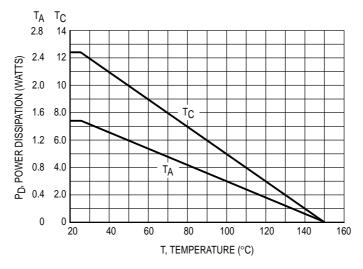


Figure 1. Power Derating

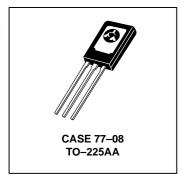
Preferred devices are Motorola recommended choices for future use and best overall value.

REV 2

MJE171* MJE172* MJE181* MJE182*

*Motorola Preferred Device

3 AMPERE
POWER TRANSISTORS
COMPLEMENTARY
SILICON
60-80 VOLTS
12.5 WATTS



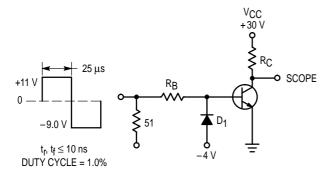


MJE171 MJE172 MJE181 MJE182

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					•
Collector–Emitter Sustaining Voltage (I _C = 10 mAdc, I _B = 0)	MJE171, MJE181 MJE172, MJE182	VCEO(sus)	60 80	_ _	Vdc
Collector Cutoff Current $(V_{CB} = 80 \text{ Vdc}, I_{E} = 0)$ $(V_{CB} = 100 \text{ Vdc}, I_{E} = 0)$ $(V_{CB} = 80 \text{ Vdc}, I_{E} = 0, T_{C} = 150^{\circ}\text{C})$ $(V_{CB} = 100 \text{ Vdc}, I_{E} = 0, T_{C} = 150^{\circ}\text{C})$	MJE171, MJE181 MJE172, MJE182 MJE171, MJE181 MJE172, MJE182	ICBO	1111	0.1 0.1 0.1 0.1	μAdc mAdc
Emitter Cutoff Current (VBE = 7.0 Vdc, I _C = 0)		I _{EBO}	_	0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain (I _C = 100 mAdc, V_{CE} = 1.0 Vdc) (I _C = 500 mAdc, V_{CE} = 1.0 Vdc) (I _C = 1.5 Adc, V_{CE} = 1.0 Vdc)		hFE	50 30 12	250 — —	_
Collector–Emitter Saturation Voltage (I _C = 500 mAdc, I _B = 50 mAdc) (I _C = 1.5 Adc, I _B = 150 mAdc) (I _C = 3.0 Adc, I _B = 600 mAdc)	- 44	VCE(sat)	_ _ _	0.3 0.9 1.7	Vdc
Base–Emitter Saturation Voltage (I _C = 1.5 Adc, I _B = 150 mAdc) (I _C = 3.0 Adc, I _B = 600 mAdc)	TE STOR	VBE(sat)	_ _	1.5 2.0	Vdc
Base–Emitter On Voltage (I _C = 500 mAdc, V _{CE} = 1.0 Vdc)		V _{BE(on)}	-	1.2	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product (1) (I _C = 100 mAdc, V _{CE} = 10 Vdc, f _{test} = 10 MHz)		fΤ	50	_	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 0.1 MHz)	MJE171/MJE172 MJE181/MJE182	C _{ob}		60 40	pF

⁽¹⁾ $f_T = |h_{fe}| \cdot f_{test}$



 R_B and R_C VARIED TO OBTAIN DESIRED CURRENT LEVELS D_1 MUST BE FAST RECOVERY TYPE, e.g.: $1N5825 \ \text{USED ABOVE } I_B \approx 100 \ \text{mA} \\ \text{MSD6100 USED BELOW } I_B \approx 100 \ \text{mA} \\ \text{FOR PNP TEST CIRCUIT, REVERSE ALL POLARITIES.}$

Figure 2. Switching Time Test Circuit

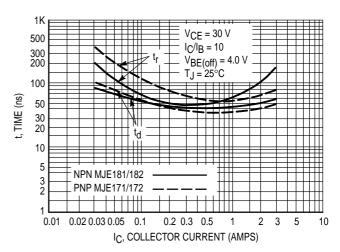


Figure 3. Turn-On Time

MJE171 MJE172 MJE181 MJE182

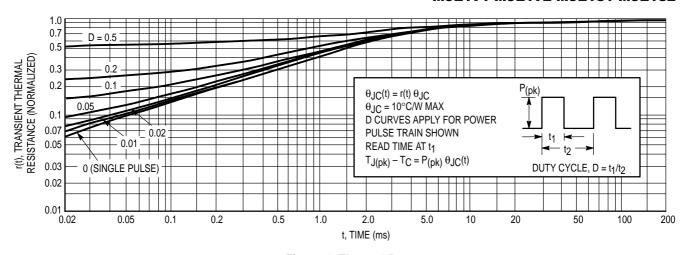


Figure 4. Thermal Response

ACTIVE-REGION SAFE OPERATING AREA

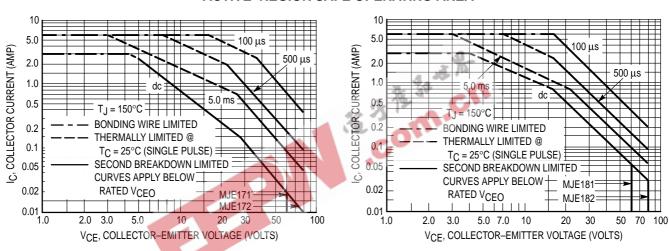


Figure 5. MJE171, MJE172

Figure 6. MJE181, MJE182

There are two limitations on the power handling ability of a transistor — average junction temperature and second breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 5 and 6 is based on $T_{J(pk)} = 150^{\circ}C$; T_{C}

is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)}$ < 150 °C. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperature, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

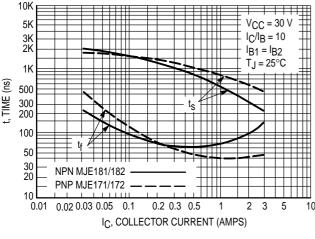


Figure 7. Turn-Off Time

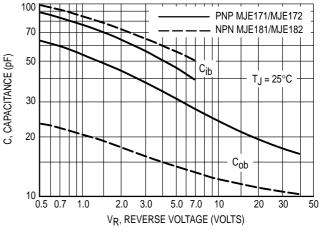
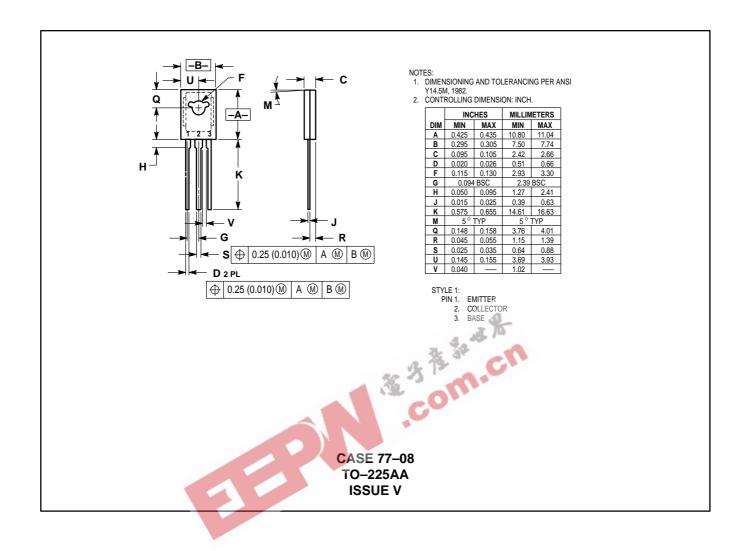


Figure 8. Capacitance

MJE171 MJE172 MJE181 MJE182

PACKAGE DIMENSIONS



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